

N-Channel Super Junction Power MOSFET $\, \mathrm{I\!V}$

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent R_{DS(ON)} with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

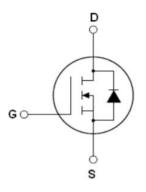
Features

- Optimized body diode reverse recovery performance
- ●Low on-resistance and low conduction losses
- ●Small package
- ●Ultra Low Gate Charge cause lower driving requirements
- ●100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge

V _{DS min@Tjmax}	550	V
RDS(ON)TYP.	2000	mΩ
I_D	1.4	Α
Qg	4.2	nC



Schematic diagram

Package Marking And Ordering Information

Device	Device Package	Marking
NCE50N2K2F	TO-220F-3L	NCE50N2K2F



TO-220F

V1.0

Table 1. Absolute Maximum Ratings (T_c=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V _{GS} =0V)	V _{DS}	500	V
Gate-Source Voltage (VDS=0V) ,AC (f>1 Hz)	Vgs	±30	V
Gate-Source Voltage (V _{DS=0} V) ,DC	Vgs	±20	V
Continuous Drain Current at Tc=25°C	I _{D (DC)}	1.4	А
Continuous Drain Current at Tc=100°C	I _{D (DC)}	0.98	А
Pulsed drain current (Note 1)	I _{DM (pluse)}	4.2	А
Maximum Power Dissipation(Tc=25℃)	P _D	7.6	W
Derate above 25°C		0.05	w/°C
Single pulse avalanche current (Note 2)	I _{AS}	1	А
Reverse diode dv/dt, $V_{DS} \le 480 \text{ V,I}_{SD} < I_D$	dv/dt	15	V/ns
Drain Source voltage slope,V _{DS} ≤480 V	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55+175	°C

V1.0



Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R _{thJC}	19.73	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R _{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
On/off states				•	'	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250uA	500			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =500V,V _{GS} =0V			1	μA
Zero Gate Voltage Drain Current(Tc=125°C)	I _{DSS}	V _{DS} =500V,V _{GS} =0V			50	μA
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm20V, V_{DS}=0V$			±200	nA
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250uA$	2.5	3.2	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =0.7A		2000	2250	mΩ
Dynamic Characteristics						
Gate Resistance	Rg	F=1MHZ, D-S short		3.1		Ω
Input Capacitance	C _{lss}	V 50VV 0V		58		pF
Output Capacitance	Coss	$V_{DS}=50V, V_{GS}=0V,$		8.6		pF
Reverse Transfer Capacitance	C _{rss}	F=1MHz		4.2		pF
Total Gate Charge	Qg			4	6	nC
Gate-Source Charge	Q _{gs}	V_{DS} =350 V , I_{D} =0.7 A ,		0.4		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V		1.6		nC
Gate plateau voltage	Vgp			4		V
Switching times						
Turn-on Delay Time	t _{d(on)}			5		nS
Turn-on Rise Time	tr	V_{DD} =380 V , I_{D} =0.7 A ,		4		nS
Turn-Off Delay Time	t _{d(off)}	$R_G=5\Omega, V_{GS}=10V$		20		nS
Turn-Off Fall Time	t _f			36		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T -05°0			1.4	Α
Pulsed-Source-drain current(Body Diode)	I _{SDM}	T _C =25°C			4.2	Α
Forward on voltage	V _{SD}	Tj=25°C,I _{SD} =1.4A,V _{GS} =0V		0.9	1.2	V
Reverse Recovery Time	t _{rr}			110		nS
Reverse Recovery Charge	Q _{rr}	Tj=25°C,I _{F=} 0.7A,		0.33		uC
Peak reverse recovery current	I _{rrm}	di/dt=100A/µs		6		Α

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25 $^{\circ}\mathrm{C}$,VDD=50V,VG=10V, R_G=25 $^{\Omega}$



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure 1. Safe operating area

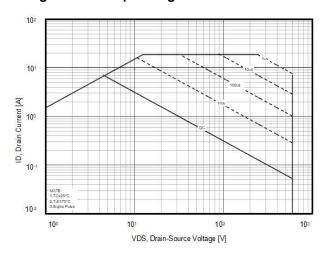


Figure 2. Source-Drain Diode Forward Voltage

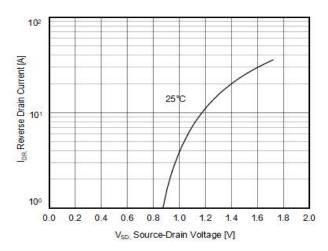


Figure 3. Output characteristics

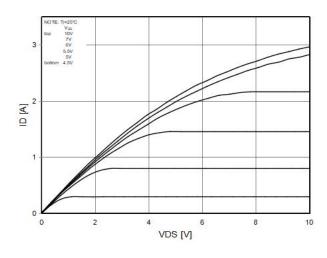


Figure 4. Transfer characteristics

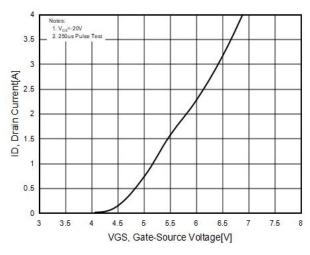


Figure 5. Static drain-source on resistance

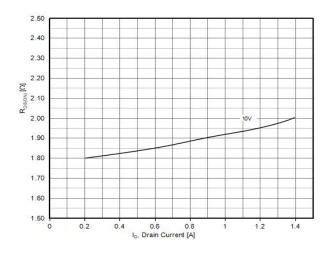


Figure 6. RDS(ON) vs Junction Temperature

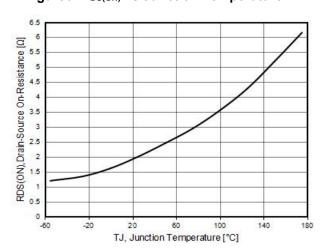




Figure 7. BV_{DSS} vs Junction Temperature

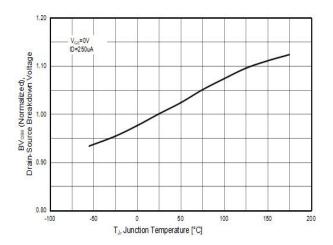


Figure 9. Gate charge waveforms

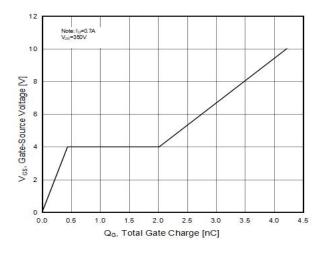


Figure 8. Maximum I_D vs Junction Temperature

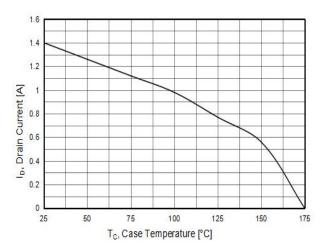
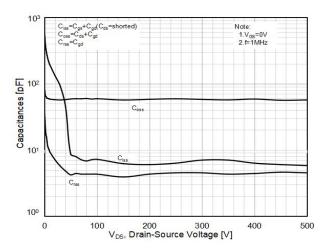


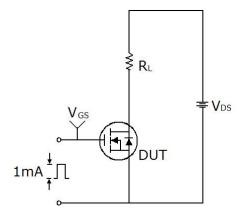
Figure 10. Capacitance

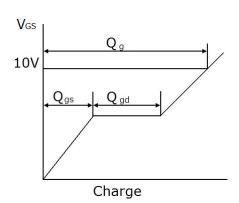




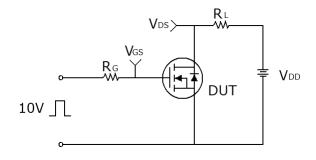
Test circuit

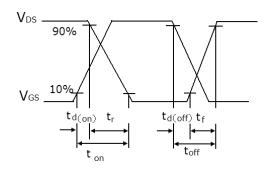
1) Gate charge test circuit & Waveform



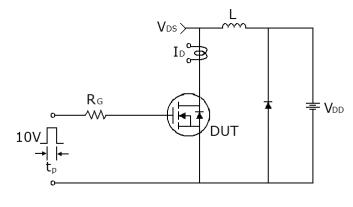


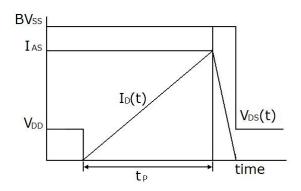
2) Switch Time Test Circuit:





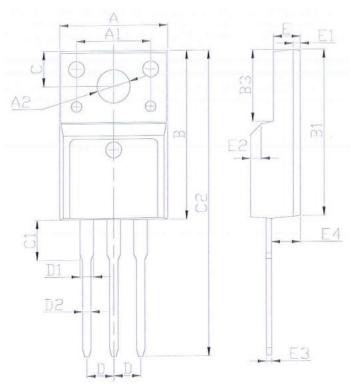
3) Unclamped Inductive Switching Test Circuit & Waveforms







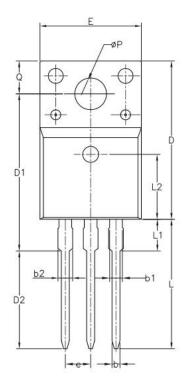
TO-220F-3L-L Package Information

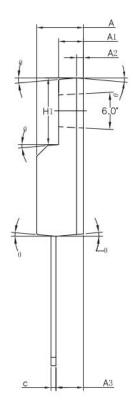


Symbol	Dimensions In Millimeters		Dimensions In Millimeters Dimensions In		s In Inches
	Min.	Max.	Min.	Max.	
А	9.86	10.46	0.387	0.411	
A1	6.80	7.20	0.267	0.283	
A2	2.92	3.32	0.115	0.130	
A3	9.40	10.00	0.369	0.393	
В	15.40	16.40	0.605	0.644	
B1	15.10	16.10	0.593	0.633	
B2	4.40	5.00	0.173	0.196	
В3	6.40	7.00	0.251	0.275	
С	3.05	3.55	0.120	0.139	
C1	2.95	3.55	0.116	0.139	
C2	28.20	29.20	1.108	1.147	
D	2.54	BSC	0.100 BSC		
D1		1.47		0.058	
D2	0.60	1.00	0.024	0.039	
E	2.30	2.80	0.090	0.110	
E1	0.45	0.95	0.018	0.037	
E2	45.0°		45.00°		
E3	0.30	0.70	0.012	0.028	
E4	2.45	3.05	0.096	0.120	



TO-220F-3L-P Package Information





Symbol	Dimensions In Millimeters		Dimensions In Inch	
	Min.	Max.	Min.	Max.
Α	4.50	4.83	0.177	0.190
A1	2.34	2.74	0.092	0.108
A2	0.70	REF	0.028	REF
A3	2.56	2.93	0.101	0.115
b	0.70	0.90	0.028	0.035
b1	1.18	1.38	0.046	0.054
b2		1.47		0.058
С	0.45	0.60	0.018	0.024
D	15.67	16.07	0.616	0.631
D1	15.55	15.95	0.611	0.627
D2	9.60	10.00	0.377	0.393
E	9.96	10.36	0.391	0.407
е	2.54	BSC	0.100) BSC
H1	6.48	6.88	0.255	0.270
L	12.68	13.28	0.498	0.522
L1		3.50		0.138
L2	6.50 REF		0.255	REF
Ø P	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



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